Amendments to the Claims

Claims 1-8 (Canceled)

9. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of sequentially:

forming a first interlayer insulating film on a semiconductor substrate;

forming a plurality of openings in said first interlayer insulating film;

forming a conductor film on said first interlayer insulating film so as to fill said openings;

removing said conductor film from ~~form~~ said surface of said first interlayer insulating film through chemical etching and forming conductor plugs from said conductor film filled in said openings;

leveling the surface of said first interlayer insulating film from which said conductor film has been removed until the surface of said first interlayer insulating film becomes flush with the surface of said conductor plugs by chemical-and-mechanical polishing:

forming a second interlayer insulating film on said first interlayer insulating film having said conductor plugs formed therein;

forming a writing pattern on said second interlayer insulating film;

forming a third interlayer insulating film on said second interlayer insulating film so as to cover said wiring pattern;

forming a plurality of openings so as to penetrate said second and third interlayer insulating films respectively to said conductor plugs; and

forming a plurality of interconnect conductors in said openings so as to be electrically connected to each of said conductor plugs.

10. (Canceled)

11. (Original) The semiconductor device manufacturing method as defined in claim 9, wherein said first interlayer insulating film is formed from a silicon oxide film containing at least phosphor.

12. (Original) The semiconductor device manufacturing method as defined in claim 9, wherein said conductor film is formed of polycrystalline or amorphous silicon.

13. (Canceled)